



60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	$23m\Omega @ V_{GS} = 10V$	50A
	$28m\Omega @ V_{GS} = 4.5V$	45A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power Management
- Driving Solenoids
- Motor Control

Features

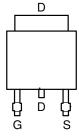
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMNH6021SK3Q</u>)

Mechanical Data

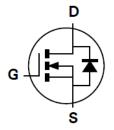
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



Equivalent Circuit

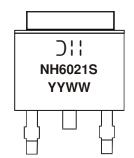
Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH6021SK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Oll =Manufacturer's Marking
NH6021S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		ID	50 35	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	80	Α	
Maximum Continuous Body Diode Forward Current (Note 7)	Is	40	Α	
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	35	Α	
Avalanche Energy, L = 0.1mH (Note 8)	Eas	64	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	73	°C/W
Total Power Dissipation (Note 6)		P _D	3.7	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{ heta JA}$	40	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.8	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		-	13	23	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Drain-Source On-Nesistance	R _{DS(ON)}	-	18	28		$V_{GS} = 4.5V, I_D = 12A$	
Diode Forward Voltage	V _{SD}	-	0.75	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	-	1143	-	рF	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	-	168	-	рF		
Reverse Transfer Capacitance	C _{rss}	-	69	-	pF		
Gate Resistance	R_g	-	2.5	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	-	20.1	-	nC		
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	12.1	-	nC		
Gate-Source Charge	Q _{gs}	-	4.3	-	nC	$V_{DS} = 30V, I_D = 20A$	
Gate-Drain Charge	Q _{gd}	-	5.5	-	nC	1	
Turn-On Delay Time	t _{D(ON)}	-	4.4	-	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $R_G = 4.7\Omega, I_D = 10A$	
Turn-On Rise Time	t _R	-	6.0	-	ns		
Turn-Off Delay Time	t _{D(OFF)}	-	14.2	-	ns		
Turn-Off Fall Time	t _F	-	5.4	-	ns		
Reverse Recovery Time	t _{RR}	-	21.2	-	ns		
Reverse Recovery Charge	Q _{RR}	-	15.2	-	nC		

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

^{7.} Thermal resistance from junction to soldering point (on the exposed drain pad).

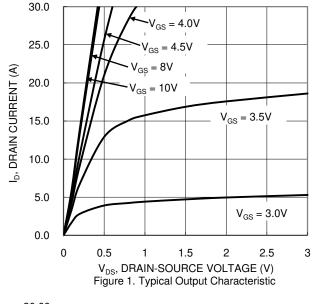
^{8.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

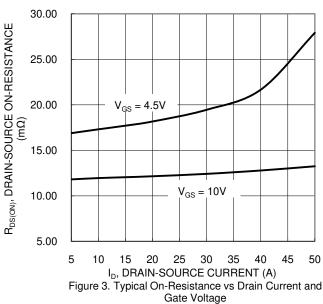
^{9.} Short duration pulse test used to minimize self-heating effect.

^{10.} Guaranteed by design. Not subject to product testing.









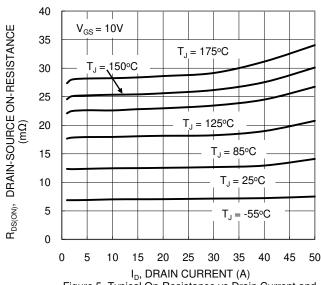
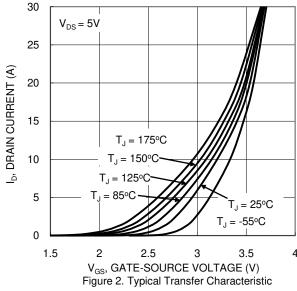
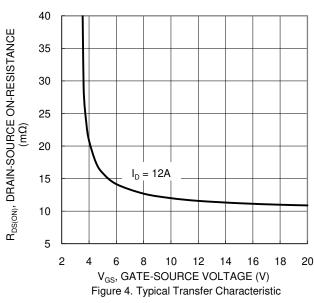


Figure 5. Typical On-Resistance vs Drain Current and Temperature





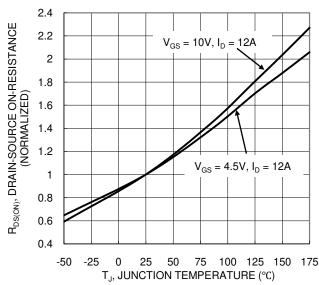
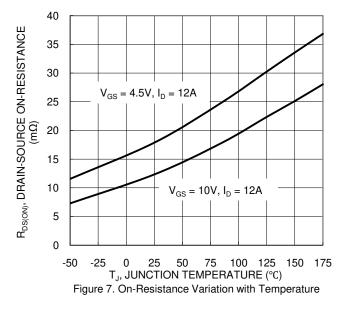
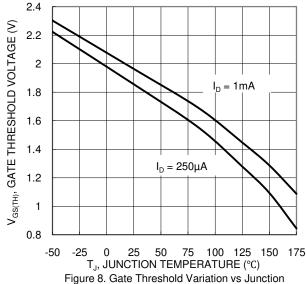


Figure 6. On-Resistance Variation with Temperature

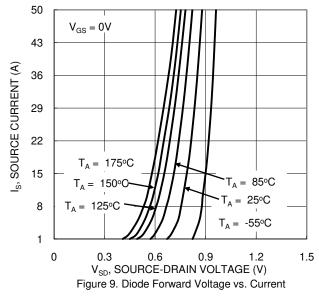


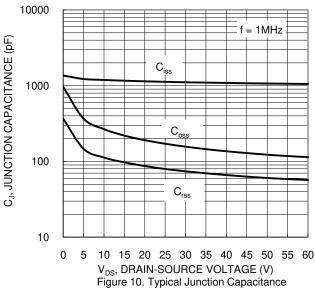


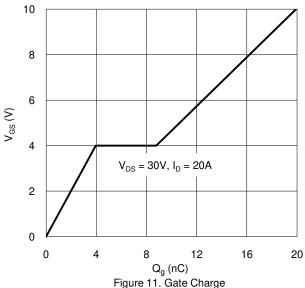


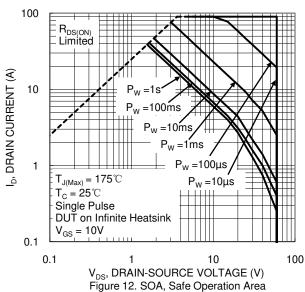


Temperature

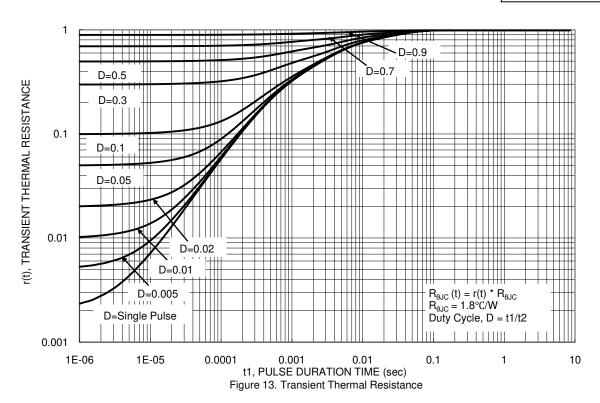










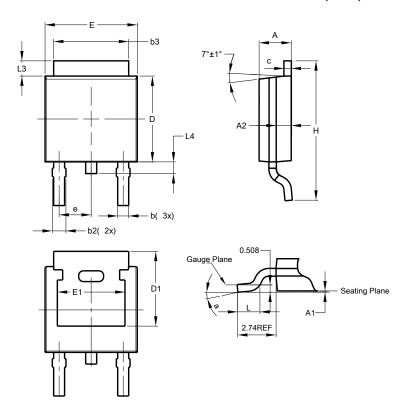




Package Outline Dimensions

 $Please see \ http://www.diodes.com/package-outlines.html \ for the \ latest \ version.$

TO252 (DPAK)

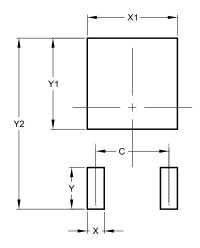


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Υ	2.600			
Y1	5.700			
Y2	10.700			



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